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| L2 | 2 | "6248383".pn. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 13:47 |
| L3 | 3 | ("3970520" "4482574" "4871575").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/10/28 13:46 |
| L6 | 72266 | ((("702") or ("705"))).CLAS. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/28 15:47 |
| L8 | 2 | L6 and (yield with (ratio percentage)) same (process\$3 with (material product)) same (raw with (material product)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 15:47 |
| S1 | 136 | zhang-xin\$.in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/27 14:04 |
| S2 | 23320 | fujitsu with limited\$.as. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/27 14:04 |
| S4 | 1 | 10/749550 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/27 14:29 |
| S9 | 2 | (S1 S2) and (yield with percentage) and (control\$4 process\$3) and ((updat\$3 calibrat\$3 correct\$3) same (yield with percentage)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/27 14:34 |
| S10 | 221 | (yield with percentage) and (control\$4 process\$3) and ((updat\$3 calibrat\$3 correct\$3) same (yield with percentage)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/27 14:34 |
| S11 | 18 | (yield with percentage) and (raw with material) and (control\$4 process\$3) and ((updat\$3 calibrat\$3 correct\$3) same (yield with percentage)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/27 14:55 |

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|-----|-----|---|---|----|----|------------------|
| S12 | 16 | (yield with percentage) and (raw with material) and (control\$4 process\$3) and ((updat\$3 calibrat\$3 correct\$3) same (yield with percentage)) and ((K with value)weight) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/27 14:57 |
| S17 | 21 | (yield same percentage) and (raw with material) and (control\$4 process\$3) and ((record\$3 updat\$3 calibrat\$3 correct\$3) same yield same percentage) and (K weight) not S12 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/27 15:41 |
| S18 | 14 | (yield same percentage) and (control\$4 process\$3) and ((record\$3 updat\$3 calibrat\$3 correct\$3) same yield) and ((K with factor) same weight) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 07:01 |
| S21 | 14 | (yield same percentage) and (control\$4 process\$3) and ((record\$3 updat\$3 calibrat\$3 correct\$3) same yield) and ((K with factor) same weight) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 07:02 |
| S24 | 326 | ((yield with (ratio percentage)) same (control\$4 process\$3) same (record\$3 updat\$3 calibrat\$3 correct\$3)) and ("K" weight) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 07:06 |
| S25 | 67 | (yield with (ratio percentage)) same (control\$4 process\$3) same (record\$3 updat\$3 calibrat\$3 correct\$3) same ("K" weight) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 07:06 |
| S26 | 8 | ((yield with (ratio percentage)) same (control\$4 process\$3) same (record\$3 updat\$3 calibrat\$3 correct\$3) same ("K" weight)) and (raw with material) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 09:02 |
| S27 | 227 | ((yield same (ratio percentage)) same (control\$4 process\$3) same (record\$3 updat\$3 calibrat\$3 correct\$3) same ("K" weight)) not S26 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 09:10 |
| S28 | 59 | ((yield with(ratio percentage)) same (control\$4 process\$3) same (record\$3 updat\$3 calibrat\$3 correct\$3) same ("K" weight)) not S26 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 09:11 |
| S32 | 1 | sawazaki-hideki\$.in. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 13:46 |

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|-----|------|--|---|----|----|------------------|
| S33 | 6 | ((yield with(ratio percentage)) same (control\$4 process\$3) same (record\$3 updat\$3 calibrat\$3 correct\$3) same ("K" weight)) and processed and raw | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 09:31 |
| S35 | 24 | (yield same (ratio percentage) same manage\$4) and ((processed raw)with material) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 10:11 |
| S36 | 12 | (percentage with raw with (material product) with produce with process\$3 with (material product)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 10:23 |
| S38 | 3730 | (yield with (ratio percentage)) and (process\$3 with (material product)) and (raw with (material product)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 10:25 |
| S39 | 154 | (yield with (ratio percentage)) same (process\$3 with (material product)) same (raw with (material product)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 15:47 |
| S40 | 4 | (yield with (ratio percentage)) same (process\$3 adj (material product)) same (raw adj (material product)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 10:26 |
| S41 | 10 | (yield with (ratio percentage)) same (process\$3 near (material product)) same (raw near (material product)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 10:32 |
| S42 | 41 | (yield with (ratio percentage)) and ((process\$3 adj (material product)) same (raw adj (material product))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 10:33 |
| S43 | 8 | (yield adj (ratio percentage)) and ((process\$3 adj (material product)) same (raw adj (material product))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2005/10/28 15:47 |


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